

Laurence Eaves

List of Publications by Year in descending order

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456
papers

16,942
citations

28274

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18647

119
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all docs

459
docs citations

459
times ranked

13997
citing authors

#	ARTICLE	IF	CITATIONS
1	Exciton and Phonon Radiative Linewidths in Monolayer Boron Nitride. <i>Physical Review X</i> , 2022, 12, .	8.9	5
2	Heavy carrier effective masses in van der Waals semiconductor Sn(SeS) revealed by high magnetic fields up to 150 T. <i>Physical Review B</i> , 2021, 104, .	3.2	1
3	Graphene's non-equilibrium fermions reveal Doppler-shifted magnetophonon resonances accompanied by Mach supersonic and Landau velocity effects. <i>Nature Communications</i> , 2021, 12, 6392.	12.8	5
4	Van der Waals SnSe 2(1 \times) S 2 x Alloys: Composition-Dependent Bowing Coefficient and Electron-Phonon Interaction. <i>Advanced Functional Materials</i> , 2020, 30, 1908092.	14.9	18
5	Defect-Assisted High Photoconductive UV-Visible Gain in Perovskite-Decorated Graphene Transistors. <i>ACS Applied Electronic Materials</i> , 2020, 2, 147-154.	4.3	13
6	Resonant tunnelling into the two-dimensional subbands of InSe layers. <i>Communications Physics</i> , 2020, 3, .	5.3	22
7	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. <i>Nano Letters</i> , 2019, 19, 6475-6481.	9.1	32
8	Strong magnetophonon oscillations in extra-large graphene. <i>Nature Communications</i> , 2019, 10, 3334.	12.8	25
9	Magnetophonon spectroscopy of Dirac fermion scattering by transverse and longitudinal acoustic phonons in graphene. <i>Physical Review B</i> , 2019, 100, .	3.2	16
10	Direct band-gap crossover in epitaxial monolayer boron nitride. <i>Nature Communications</i> , 2019, 10, 2639.	12.8	162
11	Photoquantum Hall Effect and Light-Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. <i>Advanced Functional Materials</i> , 2019, 29, 1805491.	14.9	20
12	High-order fractal states in graphene superlattices. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2018, 115, 5135-5139.	7.1	63
13	High-temperature molecular beam epitaxy of hexagonal boron nitride layers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018, 36, .	1.2	31
14	Lattice-Matched Epitaxial Graphene Grown on Boron Nitride. <i>Nano Letters</i> , 2018, 18, 498-504.	9.1	39
15	Tunnel spectroscopy of localised electronic states in hexagonal boron nitride. <i>Communications Physics</i> , 2018, 1, .	5.3	33
16	High-Temperature Molecular Beam Epitaxy of Hexagonal Boron Nitride with High Active Nitrogen Fluxes. <i>Materials</i> , 2018, 11, 1119.	2.9	17
17	Magnon-assisted tunnelling in van der Waals heterostructures based on CrBr ₃ . <i>Nature Electronics</i> , 2018, 1, 344-349.	26.0	239
18	Moiré-Modulated Conductance of Hexagonal Boron Nitride Tunnel Barriers. <i>Nano Letters</i> , 2018, 18, 4241-4246.	9.1	19

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19	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. <i>Physical Review Letters</i> , 2017, 119, 157701.	7.8	44
20	An atomic carbon source for high temperature molecular beam epitaxy of graphene. <i>Scientific Reports</i> , 2017, 7, 6598.	3.3	16
21	High-temperature quantum oscillations caused by recurring Bloch states in graphene superlattices. <i>Science</i> , 2017, 357, 181-184.	12.6	117
22	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. <i>Nature Nanotechnology</i> , 2017, 12, 223-227.	31.5	996
23	Hexagonal Boron Nitride Tunnel Barriers Grown on Graphite by High Temperature Molecular Beam Epitaxy. <i>Scientific Reports</i> , 2016, 6, 34474.	3.3	60
24	High temperature MBE of graphene on sapphire and hexagonal boron nitride flakes on sapphire. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, .	1.2	22
25	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. <i>Scientific Reports</i> , 2016, 6, 39619.	3.3	150
26	Strain-Engineered Graphene Grown on Hexagonal Boron Nitride by Molecular Beam Epitaxy. <i>Scientific Reports</i> , 2016, 6, 22440.	3.3	49
27	Resonant Zener tunnelling via zero-dimensional states in a narrow gap diode. <i>Scientific Reports</i> , 2016, 6, 32039.	3.3	4
28	Tuning the valley and chiral quantum state of Dirac electrons in van der Waals heterostructures. <i>Science</i> , 2016, 353, 575-579.	12.6	88
29	Phonon-Assisted Resonant Tunneling of Electrons in Grapheneâ€“Boron Nitride Transistors. <i>Physical Review Letters</i> , 2016, 116, 186603.	7.8	78
30	The apparent fine-tuning of the cosmological, gravitational and fine structure constants. <i>Physica A: Statistical Mechanics and Its Applications</i> , 2016, 443, 355-357.	2.6	3
31	High Broadâ€“Band Photoresponsivity of Mechanically Formed InSeâ€“Graphene van der Waals Heterostructures. <i>Advanced Materials</i> , 2015, 27, 3760-3766.	21.0	320
32	Ligandâ€“Induced Control of Photoconductive Gain and Doping in a Hybrid Grapheneâ€“Quantum Dot Transistor. <i>Advanced Electronic Materials</i> , 2015, 1, 1500062.	5.1	59
33	Monte Carlo Study on Anomalous Carrier Diffusion in Inhomogeneous Semiconductors. <i>Journal of Physics: Conference Series</i> , 2015, 647, 012059.	0.4	0
34	Resonant tunnelling between the chiral Landau states of twisted graphene lattices. <i>Nature Physics</i> , 2015, 11, 1057-1062.	16.7	64
35	Graphene-hexagonal boron nitride resonant tunneling diodes as high-frequency oscillators. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	58
36	Room Temperature Electroluminescence from Mechanically Formed van der Waals IIIâ€“VI Homojunctions and Heterojunctions. <i>Advanced Optical Materials</i> , 2014, 2, 1064-1069.	7.3	71

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37	Quantum confined acceptors and donors in InSe nanosheets. Applied Physics Letters, 2014, 105, 221909.	3.3	58
38	Quantum oscillations in the photocurrent of GaAs/AlAs p-n diodes. Physical Review B, 2014, 89, .	3.2	11
39	Impact ionization and large room-temperature magnetoresistance in micron-sized high-mobility InAs channels. Physical Review B, 2014, 90, .	3.2	6
40	Twist-controlled resonant tunnelling in graphene/boron nitride/graphene heterostructures. Nature Nanotechnology, 2014, 9, 808-813.	31.5	435
41	Nonequilibrium green function simulations of graphene-nanoribbon resonant-tunneling transistors. Japanese Journal of Applied Physics, 2014, 53, 04EN04.	1.5	4
42	Tuning the Bandgap of Exfoliated InSe Nanosheets by Quantum Confinement. Advanced Materials, 2013, 25, 5714-5718.	21.0	512
43	Meristematic cell proliferation and ribosome biogenesis are decoupled in diamagnetically levitated Arabidopsis seedlings. BMC Plant Biology, 2013, 13, 124.	3.6	33
44	Vertical field-effect transistor based on graphene-WSe ₂ heterostructures for flexible and transparent electronics. Nature Nanotechnology, 2013, 8, 100-103.	31.5	1,543
45	Resonant tunnelling and negative differential conductance in graphene transistors. Nature Communications, 2013, 4, 1794.	12.8	542
46	Field-effect control of tunneling barrier height by exploiting graphene's low density of states. Journal of Applied Physics, 2013, 113, .	2.5	35
47	Theory of Resonant Tunneling through a Donor State. Japanese Journal of Applied Physics, 2012, 51, 02BJ02.	1.5	0
48	Laser Location and Manipulation of a Single Quantum Tunneling Channel in an InAs Quantum Dot. Physical Review Letters, 2012, 108, 117402.	7.8	14
49	Probing the sensitivity of electron wave interference to disorder-induced scattering in solid-state devices. Physical Review B, 2012, 85, .	3.2	8
50	Nanoengineering the built-in electric field of a photonic device by interstitial-ion diffusion. Physical Review B, 2012, 85, .	3.2	0
51	Effect of magnetically simulated zero-gravity and enhanced gravity on the walk of the common fruitfly. Journal of the Royal Society Interface, 2012, 9, 1438-1449.	3.4	16
52	Subterahertz Acoustical Pumping of Electronic Charge in a Resonant Tunneling Device. Physical Review Letters, 2012, 108, 226601.	7.8	33
53	Shape oscillations of an electrically charged diamagnetically levitated droplet. Applied Physics Letters, 2012, 100, 114106.	3.3	8
54	Microgravity simulation by diamagnetic levitation: effects of a strong gradient magnetic field on the transcriptional profile of Drosophila melanogaster. BMC Genomics, 2012, 13, 52.	2.8	47

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55	Field-Effect Tunneling Transistor Based on Vertical Graphene Heterostructures. <i>Science</i> , 2012, 335, 947-950.	12.6	2,268
56	Addendum to "Vibrations of a diamagnetically levitated water droplet", <i>Physical Review E</i> , 2012, 85, 017301.	2.1	3
57	Linear magnetoresistance due to multiple-electron scattering by low-mobility islands in an inhomogeneous conductor. <i>Nature Communications</i> , 2012, 3, 1097.	12.8	76
58	Electron Tunneling through Ultrathin Boron Nitride Crystalline Barriers. <i>Nano Letters</i> , 2012, 12, 1707-1710.	9.1	724
59	Cyclotron resonance mass and Fermi energy pinning in the In(AsN) alloy. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	11
60	Magnetic Field Modulated Photoreflectance Study of the Electron Effective Mass in Dilute Nitride Semiconductors. <i>AIP Conference Proceedings</i> , 2011, , .	0.4	3
61	Ultrafast Acoustic Gating of Photocurrent in Nanodevices With a Quantum Well. <i>AIP Conference Proceedings</i> , 2011, , .	0.4	0
62	Electronic energy levels, wavefunctions and potential landscape of nanostructures probed by magneto-tunnelling spectroscopy. <i>Journal of Physics: Conference Series</i> , 2011, 334, 012010.	0.4	0
63	TEM of Nano-LEDs made by laser writing. <i>Journal of Physics: Conference Series</i> , 2011, 326, 012055.	0.4	1
64	Picosecond strain pulses probed by the photocurrent in semiconductor devices with quantum wells. <i>Physical Review B</i> , 2011, 83, .	3.2	11
65	Diamagnetic levitation enhances growth of liquid bacterial cultures by increasing oxygen availability. <i>Journal of the Royal Society Interface</i> , 2011, 8, 334-344.	3.4	30
66	Diamagnetic levitation enhances growth of liquid bacterial cultures by increasing oxygen availability. <i>Nature Precedings</i> , 2010, , .	0.1	1
67	Manipulating and Imaging the Shape of an Electronic Wave Function by Magnetotunneling Spectroscopy. <i>Physical Review Letters</i> , 2010, 105, 236804.	7.8	18
68	Microscopic Analysis of the Valence Band and Impurity Band Theories of (Ga,Mn)As. <i>Physical Review Letters</i> , 2010, 105, 227202.	7.8	36
69	Hot electron transport and impact ionization in the narrow energy gap InAs $_{1-x}$ N $_x$ alloy. <i>Applied Physics Letters</i> , 2010, 96, 052115.	3.3	7
70	Optical Imaging of Electrical Carrier Injection into Individual InAs Quantum Dots. <i>Physical Review Letters</i> , 2010, 105, 257401.	7.8	6
71	Using randomly distributed charges to create quantum dots. <i>Physical Review B</i> , 2010, 81, .	3.2	11
72	Nanoscale Potential Fluctuations in (GaMn)As/GaAs Heterostructures: From Individual Ions to Charge Clusters and Electrostatic Quantum Dots. <i>Nano Letters</i> , 2010, 10, 4874-4879.	9.1	6

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73	Vibrations of a diamagnetically levitated water droplet. Physical Review E, 2010, 81, 056312.	2.1	41
74	Ultrafast acoustical gating of the photocurrent in an tunneling diode incorporating a quantum well. Physical Review B, 2009, 80, .	3.2	7
75	Effect of low nitrogen concentrations on the electronic properties of $\text{InAs}_{1-x}\text{N}_x$. Physical Review B, 2009, 80, .	3.2	27
76	Sensitive detection of photoexcited carriers by resonant tunneling through a single quantum dot. Physical Review B, 2009, 79, .	3.2	9
77	Tailoring the electrical conductivity of GaAs by nitrogen incorporation. Journal of Physics Condensed Matter, 2009, 21, 174209.	1.8	4
78	Carrier injection effects on exciton dynamics in GaAs/AlAs resonant-tunneling diodes. Europhysics Letters, 2009, 85, 67010.	2.0	4
79	Resonant tunneling through a dilute nitride quantum well. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 198-202.	0.8	0
80	Electron effective mass and mobility in heavily doped n-GaN probed by Raman scattering. Journal of Applied Physics, 2008, 103, 103528.	2.5	17
81	Nonaxisymmetric Shapes of a Magnetically Levitated and Spinning Water Droplet. Physical Review Letters, 2008, 101, 234501.	7.8	68
82	Fock-Darwin-Like Quantum Dot States Formed by Charged Mn Interstitial Ions. Physical Review Letters, 2008, 101, 226807.	7.8	19
83	Introduction. Carbon-based electronics: fundamentals and device applications. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 189-193.	3.4	25
84	Electron coherence length and mobility in highly mismatched III-N-V alloys. Applied Physics Letters, 2008, 93, .	3.3	17
85	High field electron dynamics in dilute nitride Ga(AsN). Applied Physics Letters, 2008, 93, .	3.3	7
86	Upconversion electroluminescence in InAs quantum dot light-emitting diodes. Applied Physics Letters, 2008, 92, .	3.3	22
87	Electron effective mass and Si-donor binding energy in $\text{GaAs}_{1-x}\text{N}_x$ probed by a high magnetic field. Physical Review B, 2008, 77, .	3.2	13
88	Bifurcations and chaos in semiconductor superlattices with a tilted magnetic field. Physical Review E, 2008, 77, 026209.	2.1	27
89	PROBING THE SCATTERING POTENTIAL OF N-IMPURITIES IN GaAs BY MAGNETO-TUNNELING. International Journal of Modern Physics B, 2007, 21, 1600-1604.	2.0	0
90	Magnetoanisotropy of electron-correlation-enhanced tunneling through a quantum dot. Physical Review B, 2007, 75, .	3.2	20

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91	Measuring the hole chemical potential in ferromagnetic Ga _{1-x} MnxAs/GaAs heterostructures by photoexcited resonant tunneling. Applied Physics Letters, 2007, 90, 082106.	3.3	12
92	Magnetic-field-induced miniband conduction in semiconductor superlattices. Physical Review B, 2007, 76, .	3.2	15
93	Magnetophonon oscillations in the negative differential conductance of dilute nitride GaAs _{1-x} N _x submicron diodes. Physical Review B, 2007, 75, .	3.2	12
94	Magnetic field tuning of hot electron resonant capture in a semiconductor device. Applied Physics Letters, 2007, 91, 142104.	3.3	5
95	Character of states near the Fermi level in (Ga,Mn)As: Impurity to valence band crossover. Physical Review B, 2007, 76, .	3.2	139
96	Alignment of Aromatic Peptide Tubes in Strong Magnetic Fields. Advanced Materials, 2007, 19, 4474-4479.	21.0	87
97	One-electron spin-dependent transport in split-gate structures containing self-organized InAs quantum dots. Journal of Experimental and Theoretical Physics, 2007, 105, 145-148.	0.9	1
98	Magnetic-field-induced Fermi-edge singularity in the tunneling current through an InAs self-assembled quantum dot. Journal of Experimental and Theoretical Physics, 2007, 105, 152-154.	0.9	4
99	Observation of the low-temperature peak in the interlayer tunneling conductance in bilayer electron systems in the absence of the magnetic field. Journal of Experimental and Theoretical Physics, 2007, 105, 177-180.	0.9	1
100	Bose condensation of excitons in two-layer electronic systems in the absence of magnetic field. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1120-1123.	0.6	0
101	Single-electron spin-dependent transport in split-gate structures containing self-assembled quantum dots. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1124-1126.	0.6	0
102	Magnetic-field-induced Fermi-edge singularity in the tunnelling current through a self-assembled InAs quantum dot. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1127-1129.	0.6	0
103	Sharp Electroluminescence Lines Excited by Tunneling Injection Into a Large Ensemble of Quantum Dots. AIP Conference Proceedings, 2007, , .	0.4	0
104	Electric-field inversion asymmetry: Rashba and Stark effects for holes in resonant tunneling devices. Physical Review B, 2006, 74, .	3.2	23
105	Raman scattering in InAs/(AlGa)As self-assembled quantum dots: Evidence of Al intermixing. Applied Physics Letters, 2006, 88, 141905.	3.3	19
106	An empire of many dimensions. Nature Materials, 2006, 5, 775-776.	27.5	2
107	Magnetotunneling spectroscopy of ring-shaped (InGa)As quantum dots: Evidence of excited states with 2p _z character. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 57-60.	2.7	0
108	Effect of inter-miniband tunneling on current resonances due to the formation of stochastic conduction networks in superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 285-288.	2.7	11

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109	Anomalous quantum Hall effect induced by nearby quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 148-151.	2.7	0
110	Optical study of resonant states in GaN x As $^{1-x}$. <i>Semiconductors</i> , 2006, 40, 1162-1164.	0.5	0
111	Strong Effect of Resonant Impurities on Landau-Level Quantization. <i>Physical Review Letters</i> , 2006, 96, 236802.	7.8	9
112	Probing the intermixing in In(Ga)As x -GaAs self-assembled quantum dots by Raman scattering. <i>Journal of Applied Physics</i> , 2006, 99, 043501.	2.5	19
113	Terahertz response of hot electrons in dilute nitride Ga(AsN) alloys. <i>Applied Physics Letters</i> , 2006, 88, 032107.	3.3	33
114	Modifying the electronic properties of GaAs x -AlAs superlattices with low-density nitrogen doping. <i>Journal of Applied Physics</i> , 2006, 100, 063718.	2.5	7
115	Voltage-controlled hole spin injection in nonmagnetic GaAs x -AlAs resonant tunneling structures. <i>Physical Review B</i> , 2006, 73, .	3.2	21
116	Sharp-line electroluminescence from individual quantum dots by resonant tunneling injection of carriers. <i>Applied Physics Letters</i> , 2006, 89, 092106.	3.3	8
117	Current flow and energy dissipation in low-dimensional semiconductor superlattices. <i>Applied Physics Letters</i> , 2006, 88, 052111.	3.3	12
118	Stochastic Carrier Dynamics in Semiconductor Superlattices. <i>Acta Physica Polonica A</i> , 2006, 109, 43-52.	0.5	0
119	Charge buildup effects in asymmetric p-type resonant tunneling diodes. <i>Microelectronics Journal</i> , 2005, 36, 356-358.	2.0	0
120	Electrical characterisation of (Ga,Mn,Cr)As thin films grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2005, 278, 695-698.	1.5	2
121	Transport properties of gated sub-micron mesas incorporating InAs self-assembled quantum dots that conduct near zero bias. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 26, 482-485.	2.7	2
122	Excited states of ring-shaped (InGa)As quantum dots in a GaAs x -(AlGa)As quantum well. <i>Physical Review B</i> , 2005, 72, .	3.2	13
123	Trion formation in narrow GaAs quantum well structures. <i>Physical Review B</i> , 2005, 71, .	3.2	19
124	The resonant tunneling of holes through double-barrier structures with InAs QDs at the center of a GaAs quantum well. <i>Semiconductors</i> , 2005, 39, 543-546.	0.5	0
125	Coulomb Oscillations of the Current through Spin-Nondegenerate p States of InAs Quantum Dots. <i>JETP Letters</i> , 2005, 82, 526.	1.4	0
126	Dilute Nitride Ga(AsN) Alloys: an Unusual Band Structure Probed by Magneto-Tunneling. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	0

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127	Electrical conduction properties of Ga(AsN) layers. AIP Conference Proceedings, 2005, , .	0.4	1
128	Observation of current resonances due to enhanced electron transport through stochastic webs in superlattices. AIP Conference Proceedings, 2005, , .	0.4	0
129	Raman scattering by LO phonon-plasmon coupled modes in heavily doped Ga(AsN). AIP Conference Proceedings, 2005, , .	0.4	0
130	Breakup of the conduction band structure of diluteGaAs $1\hat{\sim}y$ Nyalloys. Physical Review B, 2005, 71, .	3.2	40
131	Hot-electrons and negative differential conductance inGaAs $1\hat{\sim}x$ Nx. Physical Review B, 2005, 72, .	3.2	28
132	Effect of hydrostatic pressure on the fragmented conduction band structure of dilute Ga(AsN) alloys. Physical Review B, 2005, 72, .	3.2	20
133	Quasiballistic transport of hot holes in GaAs submicron channels. Applied Physics Letters, 2005, 86, 042101.	3.3	1
134	Spin splitting of X-valley-related donor impurity states in an AlAs barrier. Physical Review B, 2005, 71, .	3.2	10
135	Cryogenically enhanced magneto-Archimedes levitation. New Journal of Physics, 2005, 7, 118-118.	2.9	40
136	RESONANT TRANSPORT IN SEMICONDUCTOR SUPERLATTICES IN A TILTED MAGNETIC FIELD. , 2005, , .		0
137	The unusual conduction band structure of Ga(AsN) probed by magneto-tunnelling and photocurrent spectroscopy. Journal of Physics Condensed Matter, 2004, 16, S3171-S3185.	1.8	4
138	Exploring the limits of superlattice miniband engineering using inverse scattering. Semiconductor Science and Technology, 2004, 19, S91-S93.	2.0	0
139	Magnetic-Field-Induced Suppression of Electronic Conduction in a Superlattice. Physical Review Letters, 2004, 93, 146801.	7.8	13
140	Electron conduction in two-dimensionalGaAs $1\hat{\sim}y$ Nychannels. Physical Review B, 2004, 69, .	3.2	31
141	Time-resolved photoluminescence of InAs quantum dots in a GaAs quantum well. Applied Physics Letters, 2004, 84, 3046-3048.	3.3	23
142	Magnetophotoluminescence study of the influence of substrate orientation and growth interruption on the electronic properties of InAs $\hat{\sim}$ GaAs quantum dots. Journal of Applied Physics, 2004, 96, 2535-2539.	2.5	13
143	Carrier kinetics in a high-optically efficient quantum dot structure. Semiconductor Science and Technology, 2004, 19, S282-S284.	2.0	3
144	RESONANT TRANSPORT IN SEMICONDUCTOR SUPERLATTICES IN A TILTED MAGNETIC FIELD. International Journal of Modern Physics B, 2004, 18, 3617-3620.	2.0	1

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145	FURTHER EVIDENCE FOR A COLLAPSE OF THE EXCHANGE-ENHANCED SPIN SPLITTING IN TWO DIMENSIONAL SYSTEMS. <i>International Journal of Modern Physics B</i> , 2004, 18, 3597-3602.	2.0	2
146	Chaotic electron diffusion through stochastic webs enhances current flow in superlattices. <i>Nature</i> , 2004, 428, 726-730.	27.8	117
147	Use of stochastic web patterns to control electron transport in semiconductor superlattices. <i>Physica D: Nonlinear Phenomena</i> , 2004, 199, 166-172.	2.8	10
148	Resonance and current instabilities in AlN/GaN resonant tunnelling diodes. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 21, 752-755.	2.7	19
149	Probing the N-induced states in dilute GaAsN alloys by magneto-tunnelling. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 21, 892-896.	2.7	0
150	Study of electron dynamics in n-type GaN using the Osaka free electron laser. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2004, 528, 623-626.	1.6	0
151	Magneto-photoluminescence of stacked self-assembled InAs/GaAs quantum dots. <i>Physica B: Condensed Matter</i> , 2004, 346-347, 428-431.	2.7	10
152	Nonequilibrium Green's function approach to resonant transport in semiconductor superlattices. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 21, 717-721.	2.7	1
153	Light-emitting diodes based on GaMnAs/GaAs heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 21, 1002-1006.	2.7	1
154	Model for breakdown of laminar flow of a quantum Hall fluid around a charged impurity: comparison with experiment. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 205-209.	2.7	1
155	Magneto-tunnelling spectroscopy of nitrogen clusters in Ga(AsN) alloys. <i>IEE Proceedings: Optoelectronics</i> , 2003, 150, 49.	0.8	4
156	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. <i>Journal of Crystal Growth</i> , 2003, 251, 155-160.	1.5	32
157	Current-voltage instabilities in GaN/AlGaIn resonant tunnelling structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2389-2392.	0.8	52
158	Floating gold in cryogenic oxygen. <i>Nature</i> , 2003, 422, 579-579.	27.8	70
159	Magneto-photoluminescence studies of the influence of substrate orientation on the growth of InAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , 2003, 251, 186-191.	1.5	0
160	Emission energy and polarization tuning of InAs/GaAs self-assembled quantum dots by growth interruption. <i>Journal of Crystal Growth</i> , 2003, 251, 192-195.	1.5	8
161	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. <i>Applied Physics Letters</i> , 2003, 83, 3069-3071.	3.3	36
162	Nonlinear hole transport through a submicron-size channel. <i>Applied Physics Letters</i> , 2003, 82, 925-927.	3.3	1

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163	Investigation of radiative recombination from Mn-related states in Ga _{1-x} MnxAs. Applied Physics Letters, 2003, 83, 866-868.	3.3	5
164	Magnetic-field-induced recovery of resonant tunneling into a disordered quantum well subband. Physical Review B, 2003, 68, .	3.2	11
165	Probing the effective mass anisotropy of electrons in a GaAs/(AlGa)As quantum well. Physical Review B, 2003, 67, .	3.2	4
166	Comment on "AlN/GaN double-barrier resonant tunneling diodes grown by rf-plasma-assisted molecular-beam epitaxy" [Appl. Phys. Lett. 81, 1729 (2002)]. Applied Physics Letters, 2003, 83, 3626-3627.	3.3	37
167	Spatial mapping of the electron eigenfunctions in InAs self-assembled quantum dots by magnetotunnelling. Nanotechnology, 2003, 14, 16-19.	2.6	3
168	Dependence of quantum-dot formation on substrate orientation studied by magnetophotoluminescence. Applied Physics Letters, 2002, 81, 1480-1482.	3.3	12
169	Tailoring the electronic properties of GaAs/AlAs superlattices by InAs layer insertions. Applied Physics Letters, 2002, 81, 661-663.	3.3	36
170	Controlling the electron tunneling through InAs self-assembled dots. Journal of Applied Physics, 2002, 91, 3474-3476.	2.5	4
171	<title>Effective mass anisotropy of T-electrons in GaAs/AlGaAs quantum well with InAs layer</title> . , 2002, , .		0
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